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(54) **ACTIVE-RAY-SENSITIVE OR RADIATION-SENSITIVE RESIN COMPOSITION, RESIST FILM, PATTERN FORMATION METHOD, AND METHOD FOR MANUFACTURING ELECTRONIC DEVICE**

(71) Applicant: **FUJIFILM Corporation**, Tokyo (JP)

(72) Inventors: **Daisuke ASAKAWA**, Haibara-gun (JP); **Hironori OKA**, Haibara-gun (JP); **Kyohei SAKITA**, Haibara-gun (JP); **Michihiro SHIRAKAWA**, Haibara-gun (JP); **Akiyoshi GOTO**, Haibara-gun (JP)

(73) Assignee: **FUJIFILM Corporation**, Tokyo (JP)

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(57) **ABSTRACT**

An object of the present invention is to provide an actinic ray-sensitive or radiation-sensitive resin composition which is capable of forming a pattern having an excellent pattern line width roughness (LWR). In addition, another object of the present invention is to provide:

a resist film, a pattern forming method, and a method for manufacturing an electronic device, each of which uses the actinic ray-sensitive or radiation-sensitive resin composition.

The actinic ray-sensitive or radiation-sensitive resin composition of the present invention includes a resin including a repeating unit derived from a monomer having a salt structure and a repeating unit having a group whose polarity increases through decomposition by the action of an acid,

the salt structure consists of an anionic structure moiety and an actinic ray-sensitive decomposable or radiation-sensitive decomposable cationic structure moiety, and

a pKa of a monomer obtained by substituting the cationic structure moiety in the salt structure with a hydrogen atom is −0.80 or more.